

LAST: 1002001/Asymmetric tunneling insulator (US 2003/012001)

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S1: (1) 09/048877
S2: (1736) "KONINKLIJKE PHILIPS".as.
S3: (175943) ((barrier near (height tunnel)) tunnel\$4 ((energy diagram
S4: (39120) ((barrier near (height tunnel\$4)) ((energy diagram cond
S5: (6082820) different second
S6: (1448) (different second) adj (((barrier near (height tunnel\$4)) ((
S7: (43918) float\$4 adj (gate electrode plate trap\$4) FG
S8: (187632) (control adj (gate electrode plate) CG word adj line wordli
S9: (8) ((different second) adj (((barrier near (height tunnel\$4)) ((en
S10: (11) ((different second) adj (((barrier near (height tunnel\$4)) ((
S11: (14) ((different second) adj (((barrier near (height tunnel\$4)) ((
S12: (5) ((different second) adj (((barrier near (height tunnel\$4)) ((
S13: (9) (((different second) adj (((barrier near (height tunnel\$4)) ((
S14: (4) ("6481931" *8586797").pn.
S15: (26007) micron.as.
S16: (71272) erase
S17: (295786) retent\$4
S18: (46938) (float\$4 adj (gate electrode plate trap\$4) FG)

(((barrier near (height tunnel)) tunnel\$4 ((energy diagram conduct\$4 gap width) near band) bandgap
bandwidth (work adj function))
) near6 erase) same ((float\$4 adj (gate electrode plate trap\$4) FG)
) same (((barrier near (height tunnel)) tunnel\$4 ((energy diagram conduct\$4 gap width) near band)
bandgap bandwidth (work adj function))
) near6 retent\$4)

Feb. 2003

	U	Inventor	Document	Issue	P	Title	Current	Current X	Retrieval	S	C	P	Image	Do	P
1		Chindalore, US	200301	2003	6	Non-volatile memory device with impro	438/20	257/E29.1						US 20030	
2		Nakazato, US	657414	2003	1	Memory device using hot charge carri	365/18	257/315						US 65741	
3		Rudeck, Pa	US 200500	2005	2	Methods and structure for an improve	438/26	438/260						US 20050	
4		Chindalore, US	200401	2004	6	Non-volatile memory device with impro	257/32	257/321						US 20040	
5		Hyde, John	US 200400	2004	3	Pseudo-nonvolatile direct-tunneling flo	257/31	257/E29.3						US 20040	
6		Forbes, Le	US 200302	2003	2	Write once read only memory with larg	257/31	257/314						US 20030	
7		Rudeck, Pa	US 200302	2003	2	Method and structure for an improved	438/20	257/E21.6						US 20030	
8		Mihnea, An	US 200300	2003	1	Flash memory cell for high efficiency p	365/18	365/185.0						US 20030	
9		Mihnea, An	US 200300	2003	1	Flash memory cell for high efficiency p	365/18							US 20030	
10		Forbes, Le	US 200201	2002	2	P-channel dynamic flash memory cells	257/31	257/E21.2						US 20020	